IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of:

Wai M. LEE et al.

Confirmation No.:

8883

Serial No.:

09/988,545 10 826 286

Art Unit:

1751

Filed:

November 20, 2001

Examiner:

Gregory Del Cotto

For:

CLEANING SOLUTION INCLUDING NUCLEOPHILIC AMINE COMPOUND

Atty. Docket No.: 060937-0127-US

HAVING REDUCTION AND OXIDATION **POTENTIALS**

SUBMISSION OF REVOCATION OF ORIGINAL POWER OF ATTORNEY AND GRANT OF NEW POWER OF ATTORNEY

U.S. Patent and Trademark Office Randolph Building, 401 Dulany Street Alexandria, Virginia 22314

Sir:

Enclosed is a copy of a Revocation of Original Power of Attorney and Grant of New Power of Attorney by the Assignee, EKC Technology, Inc. The instant application is a continuation of 09/988,545, which is listed on the attached Schedule A. Assignee directs the Patent and Trademark Office to send all future correspondence to:

> CUSTOMER NO. 009629 MORGAN, LEWIS & BOCKIUS LLP 1111 Pennsylvania Avenue, N.W. Washington, D.C. 20004 Tel. 202-739-3000

If there is any fee due in connection with the filing of this Submission, please charge the fee to Morgan, Lewis & Bockius LLP Deposit Account No. 50-0310.

Respectfully submitted.

Date:

February 28, 2005

Christopher Mayden

Morgan, Lewis & Bockius LLP 1111 Pennsylvania Avenue, N.W.

Washington, D.C. 20004

(202) 739-3001

CERTIFICATION OF FACSIMILE TRANSMISSION UNDER 37 C.F.R. 1.8(a)

I hereby certify that this paper is being filed with the United States Patent and Trademark Office by facsimile transmission on February 28, 2005 to facsimile telephone number 571-273-1312.

Christopher G Mayden

1-WA/2348876.1

REVOCATION AND POWER OF ATTORNEY

Commissioner for Patents P. O. Box 1450 Alexandria, Virginia 22313-1450

Sir:

EKC Technology, Inc., owner of the entire right, title and interest in, to and under the inventions described and claimed in the patent applications identified in the attached Schedule A, hereby revokes all previous powers of attorney and appoints Morgan, Lewis & Bockius LLP, Customer Number 009629, and each of them, its attorneys, to prosecute each of these patent applications, and to transact all business in the Patent and Trademark Office connected therewith.

Please direct all future correspondence to Customer No. 009629, Patent Support Unit, Morgan, Lewis & Bockius LLP, 1111 Pennsylvania Avenue, N.W., Washington, D.C. 20004, and direct all telephone calls to Morgan, Lewis & Bockius LLP at 202-739-3000.

Assignee;

EKC Technology, Inc.

Date: 29 March 2004

Signature:

Typed Name Michael A. Fury

Position/Title Vice President, R&D and Engineering

Address:

2520 Barrington Court . Hayward, California 94545

Schedule A					
2002		Solvenions), ve	- Filips Date	Neva Vibriev Dodreit Vo	Edmerationey
	Compositions for Cleaning Organic				
09/903,064	and Plasma Etched Residues for Semiconductor Devices	Small, et al.	07/10/2001	60937-091-US	8317-091-999
00,000,00	Method of and Apparatus for	Official Octob	07,10,2007	00007 007 00	0011-001-000
09/874,330		Maloney, et al.	06/06/2001	60937-111-US	8317-111-999
	Chemical Mechanical Polishing				
09/985,870	Oxalic Acid as a Semiagueous	Small, et al.	11/06/2001	60937-114-US	8317-114-999
•	Cleaning Product for Copper and				
10/421,708		Lee, et al.	04/24/2003	60937-116-US	8317-116-999
	Sulfoxide Pyrolid(in)one Alkanolamine				
10/193,185	Cleaner Composition	Zhou, et al.	07/12/2002	60937-118-US	8317-118-999
	Method for the Deposition of Materials				
09/876,944		Vasquez, et al.	06/08/2001	60937-120-US	8317-120-999
00/0/0,044	Post Etch Cleaning Composition for	<u> </u>	00/00/2001	00301-120-00	0317-120-599
10/007,134	Dual Damascene System	Payne, et al.	12/04/2001	60937-123-US	8317-123-999
	Photolytic Conversion Process to				
10/263,701		Bravo-Vasquez, et al.	10/04/2002	60937-126-US	8317-126-999
1	Cleaning Solutions Including Nucleophilic Amine Compound	j			
ĺ	Having Reduction and Oxidation				
09/988,545		Lee, et al.	. 11/20/2001	60937-127-US	8317-127-999
	Method and Compositions for				
	Chemically Treating A Substrate				
10/060,109		Patel, et al.	01/28/2002	60937-129-US	8317-129-999
1	Cleaning Solution Including Nucleophilic Amine Compound				1
	Having Reduction and Oxidation				
10/135,695		Lee, et al.	05/01/2002	60937-135-US	8317-135-999
10/448,127	Fluoride Layer and Removing Same	Melvin K. Carter	05/30/2003	60937-137-US	8317-137-999
	Process for the Use of Bis-Choline				
·	and Tris-Choline in the Cleaning of	ļ			
10/689,657	Quartz-Coated Polysilicon and Other	2 5	40/00//000		
10/069,05/	Materials Cleaning Compositions Containing	Charm, et al.	10/22/2003	60937-139-US	8317-139-999
•	Hydroxylamine Derivatives and	į	ŀ		
	Process Using Same for Residue				į.
10/689,620	Removal	Zhou, et al.	10/22/2003	60937-140-US	8317-140-999
· •	Companies for Fredrick Association]		· .
10/689,616	Composition for Exfoliation Agent to be Used to Remove Resist Residues	Mohin K Cortor	10/22/2002	60097 444 UC	0247 444 000
10003,010	Reducing Oxide Loss When Using	Melvin K. Carter	10/22/2003	60937-141-US	8317-141-999
	Fluoride Chemistries to Remove Post-	•	ļ		
j	Etch Residues in Semiconductor		· į		· j
60/467,131	Processing	Lee, et al.	05/02/2003	60937-142-PR	8317-142-888

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	Method for Depositing Patterned				SINGLE STOREL STORE
10/630,30		Hill, et al.	-07/30/2003	60937-143-US	8317-143-999
	Methods for the Deposition of Silver	<u>,,,</u>	1	00351-145-00	0517-143-999
!	and Silver Oxide Films and Patterned		1 .	.	•
10/716,83	8 Films	Ruan, et al.	11/18/2003	60937-147-US	8317-147-999
	Semiconductor Process Residue		77.75.25.25	00007-147 00	0011-141-993
10/162,679		Lee, et al.	06/06/2002	60937-149-US	8317-149-999
1	System and Method for Cleaning				140 000
	Workpieces Using Supercritical			1	
60/469,826	6 Carbon Dioxide	Fury, et al.	05/13/2003	60937-150-PR	8317-150-888
ĺ	Abrasive-Free Chemical Mechanical				
	Polishing Composition and Polishing	1			
10/689,043	Process Containing Same	Yao, et al.	10/21/2003	60937-151-US	8317-151-999
40/200 045	NATION FOR THE STATE OF THE STA				
10/689,042	Wet Etch of Titanium-Tungsten Film	Patel, et al.	10/21/2003	60937-152-US	8317-152-999
	Mothed of Dane-Nine Managhan				
10/261,197	Method of Depositing Nanostructured Films with Embedded Nanopores	.		1.]
100201,197	Hydrothermal Treatment of	Svendsen, et al.	09/30/2002	60937-153-US	8317-153-999
10/280,270		14laha.da4 _1	40/20/20	 	
10/257,469		Mukherjee, et al.	10/23/2002	60937-167-US	8317-167-999
10/201,100	Chemical Mechanical Polishing	Daviot, et al.	10/11/2002	60937-168-US	8317-168-999
10/401,405		Small stat	00.07.0000		
75. 15.1,100	Aqueous Phosphoric Acid	Small, et al.	03/27/2003	60937-171-US	8317-171-999
	Compositions for Cleaning				
10/688,900		Daviot, et al.	10/21/2003	60007 470 110	55.5 t
· · · ·	Load Lock System for Supercritical	Daviou, Ct 21.	10/2/1/2003	60937-172-US	8317-172-999
10/465,906	Fluid Cleaning	Fury, et al.	06/18/2003	80027 475 116	0247 475 000
	Automated Dense Phase Fluid	7 41 71 01 41.	00/10/2003	60937-175-US	8317-175-999
10/465,905	Cleaning System	Fury, et al.	06/18/2003	60937-176-US	9347 478 000
	Residue Removers for		00/10/2000	00837-170-03	8317-176-999
	Electrohydrodynamic Cleaning of		Í :		
60/455,439	Semiconductors	Robert J. Small	03/18/2003	60937-178-PR	8317-178-888
	Free Radical-Forming Activator			20001-110-116	0317-170-000
	Attached to Solid and Used to	•		-	
10/361,822	Enhance CMP Formulations	Scott, et al.	02/11/2003	60037-170-110	9347 470 000
	Titanium Carboxylate Films for Use in	5,5011, 51 61	0E 11/2003	60937-179-US	8317-179-999
<u>10/377,53</u> 3	Semiconductor Processing	Hill, et al.	02/26/2003	60937-182-US	9317 193 000
10/422,860	Method of Making Barrier Layers	Maloney, et al.	05/20/2003	60937-183-US	8317-182-999 8317-183-999
·	Remover Formulation Containing		44124124	00001-100-00	0317-103-999
	Fluoride for Use During				.
60/463,739	Semiconductor Manufacturing	Hirasawa, et al.	04/18/2003	60937-185-PR	8317-185-888
1	Cleaning Composition for Removing				
·	Resists and Manufacturing Method of			ļ	
30/464,125	Semiconductor Devices	Hirasawa, et al.	04/21/2003	60937-186-PR	8317-186-888
10400 - : -	Deposition of Permanent Polymer			1000	0011-100-000
0/422,212	Structures for OLED Fabrication	Roman, et al.	04/23/2003	60937-187-US	8317-187-990
•	• •	••			4-11 101-000

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	Seimconductor Process Residue				A COUNCT 150. 7
10/442,858	Removal Composition and Process	Wai Mun Lee	05/20/2003	60937-189-US	8317-189-999
	Cleaning Compositions and Method of				100 000
10/630,300	Use Thereof	Wai Mun Lee	07/30/2003	60937-194-US	8317-194-999
	Compositions and Methods for				
	Rapidly Removing Overfilled		1		·
60/518,337		Chelle, et al.	11/10/2003	60937-200-PR	8317-200-888
1	CMP Method for Copper, Tungsten,	•			
ļ	Titanium, Polysilicon, and Other				1
1	Substrates Using Organosulfonic				
10/690,623		Carter, et al.	10/23/2003	60937-202-US	8317-202-999
	PeriodicAcid Compositions for				
Ī	Polishing Nobel Metal/High K	•	1	1	,
60/494,954		Robert J. Small	08/14/2003	60937-203-PR	8317-203-888
	Cerium Oxide Abrasives for Chemical				
60/509,920	Mechanical Polishing	Robert J. Small	10/10/2003	60937-204-PR	8317-204-888
	D	•			
	Chemical Mechanical Polishing				
60/546 700	Slurries and Cleaners Containing	.			
60/516,/36	Salicyclic Acid as a Corrosion Inhibitor	Carter, et al.	11/04/2003	60937-206-PR	8317-206-888
60/404 055	Periodic Acid Compositions for	D-1-110 H			
60/494,955	Polishing Ruthenium Substrates	Robert J. Small	08/14/2003	60937-207-PR	8317-207-888
10/000 700	Chemical Mechanical Polishing	0			•
10/683,730	Compositions and Process Alumia Abrasive for Chemical	Small, et al.	10/10/2003	60937-211-US	8317-211-999
60/514,020	Mechanical Polishing	Dhilines U. Ohelle	40074000	00000 0 (0 00	
00/314,020	. weckanical Polishing	Philippe H. Cheile	10/27/1999	60937-213-PR	8317-213-888
	Chemical Mechanical Polishing		1		·
	Sturries and Cleaners Containing				
60/502,951	Salicyclic Acid as a Corrosion Inhibitor	Tamilmani, et al.	09/16/2003	60937-214-PR	0247 044 999
00.002,001	Compositions for Chemical	raminent, etal.	09/10/2003	00931-214-PR	8317-214-888
•	Mechanical Planarization of Tantalum			j	
10/665,417	and Tantalum Nitride	Small, et al.	09/22/2003	60937-215-US	8317-215-999
	Alumina Abrasive for Chemical		00/2222	00001 210 00	0017-210-333
60/526,107	Mechanical Polishing	Chelle, et al.	12/02/2003	60937-216-PR	8317-216-888
	Particulate or Particle-Bound				2000
60/509,922	Chelating Agents	Small, et al.	10/10/2003	60937-217-PR	8317-217-888
	Particulate or Particle-Bound .		•		
10/690,626	Chelating Agents	Small, et al.	10/23/2003	60937-217-US	8317-217-999
	Chemical Mechanical Polishing of STI				
·	Features on Semiconductors: Water	· _		ļ	İ
60/533,054	Polishing with Ceria Slurries	Yu, et al	12/30/2003	60937-223-PR	8317-223-888
1	_ ,				
İ	Removal of Post Etch Residues and		ł	į	
!	Copper Contamination From Low-K	. [1		
EDIE44 DAG	Dielectrics Using Superciritcal CO2		ł	. 1	i
60/511,949	with Diketone Additives	Jerome Daviot	10/14/2003	60937-225-PR	8317-225-888
10/604 655	Method and Apparatus for Substrate	İ]		/
10/694,999	Pre-Treatment	Lee, et al.	10/29/2003	60937-226-US	8317-226-999

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	Method of Chemically Mechanically				
60/515,450	Polishing Substrates	Brandon S. Scott	10/30/2003	60937-228-PR	8317-228-888